



IXTP130N10T Information

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For Reference Only

Part Number IXTP130N10T

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 130A TO-220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IXTP130N10T Specifications

Manufacturer Part Number IXTP130N10T Manufacturer IXYS Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series TrenchMV? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 130A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 104nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5080pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 360W (Tc) Rds On (Max) @ Id, Vgs 9.1 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3		
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FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 130A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 104nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5080pF @ 25V Vgs (Max) ±30V FET Feature Power Dissipation (Max) 360W (Tc) Rds On (Max) @ Id, Vgs 9.1 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C130A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 250μAGate Charge (Qg) (Max) @ Vgs104nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5080pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Series	TrenchMV?
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Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 9.1 mOhm @ 25A, 10V Operating Temperature Supplier Device Package Package / Case 130A (Tc) 130A (Tc) 130A (Tc) 130A (Tc) 130A (Tc) 140V 145V @ 250μA 5080pF @ 25V 104nC @ 10V 5080pF @ 25V 25V 25V 25V 25V 25V 25V 25V	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 250μAGate Charge (Qg) (Max) @ Vgs104nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5080pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id 4.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 104nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5080pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 360W (Tc) Rds On (Max) @ Id, Vgs 9.1 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Current - Continuous Drain (Id) @ 25°C	130A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 5080pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 9.1 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	4.5V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	104nC @ 10V
FET Feature - Gover Dissipation (Max) 360W (Tc) Rds On (Max) @ Id, Vgs 9.1 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	5080pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 9.1 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	360W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	9.1 mOhm @ 25A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
•		Report errors?

IXTP130N10T Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXTP130N10T Payment Methods

































If you have any question about IXTP130N10T, please do not hesitate to contact us!

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